L Number	Hits	Search Text	DB	Time stamp
-	0	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same (plasma adj flood adj gun)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 11:55
_	237	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:20
_	4068	((depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) (wafer adj	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27
-	30	fabrication) ((depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) and wafer	IBM_TDB, USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:25
-	79	depolarization adj (method or process)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:25
_	90	((charge adj reduct?\$5) or depolarization) adj (method or process)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:26
-	0	(((charge adj reduct?\$5) or depolarization) adj (method or process)) and (expos?\$5 with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:27
-	11	(((charge adj reduct?\$5) or depolarization) adj (method or process)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 10:27
-	7553	(depolarization or (de adj polarization))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:03
-	6	((depolarization or (de adj polarization))) and (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 11:58
-	12	((electrostatic adj discharge) or esd) with (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:02
-	0	(polarization adj charge?) with (wafer adj fabricat?\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/27 12:03
-	1	(depolarization or (de adj polarization)) with (wafer adj fabricat?\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:05
_	0	depolarization with (wafer near2 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:08

_	37	semiconductor adj fabrication adj tool?	USPAT; US-PGPUB;	2003/03/27 12:08
			EPO; JPO; DERWENT; IBM TDB	·
]	0	(semiconductor adj fabrication adj tool?)	USPAT;	2003/03/27
		with (discharge near2 electrostatic)	US-PGPUB;	12:10
			EPO; JPO; DERWENT;	
			IBM TDB	
_	0	(semiconductor adj fabrication adj tool?)	USPAT;	2003/03/27
	,	with ((discharge near2 electrostatic) or	US-PGPUB;	12:10
		esd or (electrostatic adj discharge))	EPO; JPO; DERWENT;	
			IBM_TDB	
-	0	(semiconductor adj fabrication adj tool?)	USPAT;	2003/03/27
		<pre>same ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))</pre>	US-PGPUB; EPO; JPO;	12:11
		esd of (electrostatic adj discharge)	DERWENT;	
			IBM_TDB	/
-	207	(ion adj implantation) same ((electrostatic adj charge) or esd or	USPAT; US-PGPUB;	2003/03/27
		((electrostatic adj charge) of esd of (electrostatic adj discharge))	EPO; JPO;	12.12
			DERWENT;	
	4.71	//ion add implantation\ same	IBM_TDB USPAT;	2003/03/27
_	41	((ion adj implantation) same ((electrostatic adj charge) or esd or	US-PGPUB;	12:12
		(electrostatic adj discharge))) and	EPO; JPO;	
		plasma	DERWENT; IBM TDB	
_	1	(wafer near2 pad) with (depolarization or	USPAT;	2003/03/27
	•	(de adj polarization) or (electrostatic	US-PGPUB;	12:45
		adj discharge) or esd or (charge near2 (reduct?\$5 or neutralization)))	EPO; JPO; DERWENT;	
		(reduct?\$5 or neutralization)))	IBM TDB	
-	4	(("5089710") or ("5399871")).PN.	USPAT;	2003/03/27
			US-PGPUB; EPO; JPO;	13:25
			DERWENT;	·
			IBM_TDB USPAT;	2003/03/27
_	0	("(insulating near2 pad) with plasma").PN.	US-PGPUB;	14:36
		prasma / m.	EPO; JPO;	
			DERWENT; IBM TDB	
_	14	(insulating near2 pad) with plasma	USPAT;	2003/03/27
	1 1 1	(Tributanting treats base) until breaking	US-PGPUB;	14:38
			EPO; JPO; DERWENT;	
			IBM TDB	
_	118741	(H01L021/3065 or H01L021/205 or	USPAT;	2003/03/27
		H01L021/31 or H01L021/68).ipc.	US-PGPUB; EPO; JPO;	14:39
			DERWENT;	
			IBM_TDB	2002/02/27
-	23297	((H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.) and	USPAT; US-PGPUB;	2003/03/27
	-	plasma	EPO; JPO;	
		-	DERWENT;	
_	3	(((H01L021/3065 or H01L021/205 or	IBM_TDB USPAT;	2003/03/27
		H01L021/31 or H01L021/68).ipc.) and	US-PGPUB;	14:39
		plasma) and (insulating near3 pad?)	EPO; JPO;	
			DERWENT; IBM TDB	
_	1381	depolarization and plasma	USPĀT;	2003/10/19
			US-PGPUB; EPO; JPO;	09:18
			DERWENT;	
			IBM TDB	

				1
_	3	depolarization and (exposing near5 plasma)	USPAT; US-PGPUB;	2003/10/19 09:19
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	depolarization near10 (fabrication with	USPĀT;	2003/10/19
		plasma)	US-PGPUB; EPO; JPO;	09:20
			DERWENT;	
		1 (5-1	IBM_TDB USPAT;	2003/10/19
-	5	depolarization and (fabrication with plasma)	US-PGPUB;	09:22
			EPO; JPO;	
			DERWENT; IBM TDB	
_	181	(depolariz\$5 or neutraliz\$5) and	USPĀT;	2003/10/19
		(fabrication with plasma)	US-PGPUB; EPO; JPO;	09:27
			DERWENT;	
	50050	()	IBM_TDB USPAT;	2003/10/19
_	59258	(depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)	US-PGPUB;	09:28
		issue (simily)	EPO; JPO;	
			DERWENT; IBM TDB	
_	6779		USPAT;	2003/10/19
		near5 (charge or electrostatic)) and	US-PGPUB; EPO; JPO;	09:28
		plasma	DERWENT;	
		21.05	IBM_TDB	2003/10/19
_	758	<pre>((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10</pre>	USPAT; US-PGPUB;	09:28
		plasma	EPO; JPO;	
			DERWENT; IBM TDB	
_	2	((depolariz\$5 or neutraliz\$5 or reduc\$5)	USPAT;	2003/10/19
		near5 (charge or electrostatic)) near5 (fabrication near5 plasma)	US-PGPUB; EPO; JPO;	09:29
	ļ	(Tabrication nears plasma)	DERWENT;	
	510	(4) 2 interpretable of a moduce (5)	IBM_TDB USPAT;	2004/05/20
-	612	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5	US-PGPUB;	13:16
		plasma	EPO; JPO;	
			DERWENT; IBM TDB	
-	302	(((depolariz\$5 or neutraliz\$5 or reduc\$5)	USPĀT;	2004/05/20
		near5 (charge or electrostatic)) near5 plasma) and wafer	US-PGPUB; EPO; JPO;	13:15
		P-22-100/	DERWENT;	
	36283	(depolariz\$5 or neutraliz\$5 or reduc\$5)	IBM_TDB USPAT;	2004/05/20
_	30203	with plasma	US-PGPUB;	13:53
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	5804		USPAT; US-PGPUB;	2004/05/20
		with plasma) and fabrication	EPO; JPO;	13.10
			DERWENT;	- 1
_	7713	((depolariz\$5 or neutraliz\$5 or reduc\$5)	IBM_TDB USPAT;	2004/05/20
		with plasma) and wafer	US-PGPUB;	13:20
			EPO; JPO; DERWENT;	•
			IBM_TDB	2004/05/20
-	3067	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma) and electrostatic	USPAT; US-PGPUB;	2004/05/20
		with prasma, and erectionate	EPO; JPO;	
			DERWENT; IBM TDB	
I .	I		1 1 1 1 1 1 1 1 1 1	

_	436	((depolariz\$5 or neutraliz\$5 or reduc\$5)	USPAT;	2004/05/20
		with plasma) and misalignment	US-PGPUB;	13:34
,			EPO; JPO;	
			DERWENT;	i
			IBM TDB	
-	77	plasma with (electrostatic adj charge?)	USPĀT;	2004/05/20
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	·
]		IBM TDB	
-	2	5399871.pn.	USPAT;	2004/05/20
			US-PGPUB;	13:50
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
-	74658	(depolariz\$5 or neutraliz\$5 or reduc\$5 or	USPAT;	2004/05/20
		discharg\$5) with plasma	US-PGPUB;	13:54
1			EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
-	306		USPAT;	2004/05/20
		neutraliz\$5 or reduc\$5 or discharg\$5))	US-PGPUB;	13:55
		with plasma	EPO; JPO;	
			DERWENT;	
		700077 4 1:)	IBM_TDB	2004/06/32
-	2	ep-709877-\$.did.	USPAT;	2004/06/13
			US-PGPUB;	00:40
			EPO; JPO;	
			DERWENT; IBM TDB	
			T DM I DD	1